



SANYO Semiconductors

DATA SHEET

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LB1948M — Monolithic Digital IC 12V Low Saturation Voltage Drive Forward/Reverse Motor Driver

Overview

The LB1948M is a 2-channel low saturation voltage forward/reverse motor driver IC. It is optimal for motor drive in 12V system products and can drive either two DC motors, one DC motor using parallel connection, or a 2-phase bipolar stepping motor with 1-2 phase excitation mode drive.

Features

- Supports 12V power supply systems
- Low saturation voltage: $V_{O(sat)} = 0.5V$ (typical) at $I_O = 400mA$
- Zero current drawn in standby mode
- Braking function
- Supports parallel connection: $I_O \text{ max} = 1.6A$, $V_{O(sat)} = 0.6V$ (typical) at $I_O = 800mA$
- Built-in spark killer diode
- Built-in thermal shutdown circuit
- Miniature package: MFP-10S (6.4mm × 5.0mm)

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	$V_{CC \text{ max}}$		-0.3 to +20	V
Output voltage	V_{OUT}		-0.3 to +20	V
Input voltage	V_{IN}		-0.3 to +18	V
Ground pin source current	I_{GND}	Per channel	800	mA
Allowable power dissipation	$P_d \text{ max1}$	Independent IC	350	mW
	$P_d \text{ max2}$	Mounted on a specified board*	870	mW
Operating temperature	T_{opr}		-20 to +85	$^\circ C$
Storage temperature	T_{stg}		-40 to +150	$^\circ C$

* Specified board: 114.3mm × 76.1mm × 1.6mm, glass epoxy board.

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LB1948M

Allowable Operating Range at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V_{CC}		2.5 to 16	V
Input high-level voltage	V_{IH}		1.8 to 10	V
Input low-level voltage	V_{IL}		-0.3 to +0.7	V

Electrical Characteristics at $T_a = 25^\circ\text{C}$, $V_{CC} = 5\text{V}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Current drain	I_{CC0}	IN1, 2, 3, 4 = 0V (Standby mode)		0.1	10	μA
	I_{CC1}	*1 (Forward or reverse mode)		15	21	mA
	I_{CC2}	*2 (Brake mode)		30	40	mA
Output saturation voltage	$V_{O(sat)1}$	$I_{OUT} = 200\text{mA}$ (High Side and Low Side)		0.25	0.35	V
	$V_{O(sat)2}$	$I_{OUT} = 400\text{mA}$ (High Side and Low Side)		0.50	0.75	V
Input current	I_{IN}	$V_{IN} = 5\text{V}$		85	110	μA
Spark Killer Diode						
Reverse current	$I_S(\text{leak})$				30	μA
Forward voltage	V_{SF}	$I_{OUT} = 400\text{mA}$			1.7	V

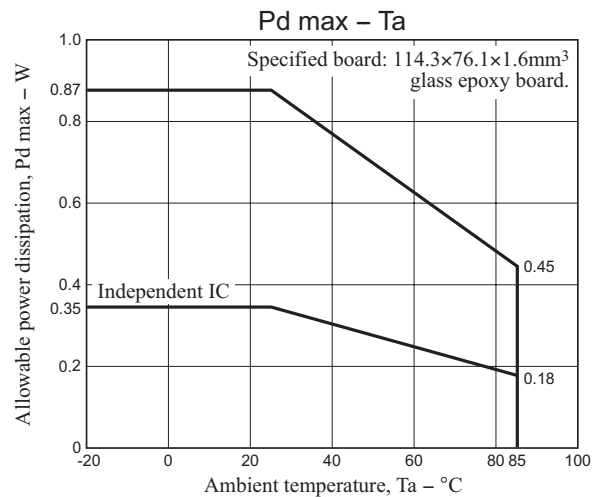
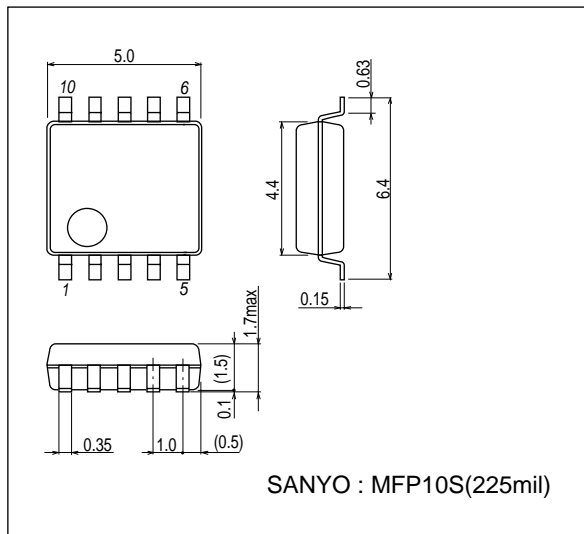
*1:IN1/IN2/IN3/IN4=H/L/L/L or L/H/L/L or L/L/H/L or L/L/L/H.

*2:IN1/IN2/IN3/IN4=H/H/L/L or L/L/H/H.

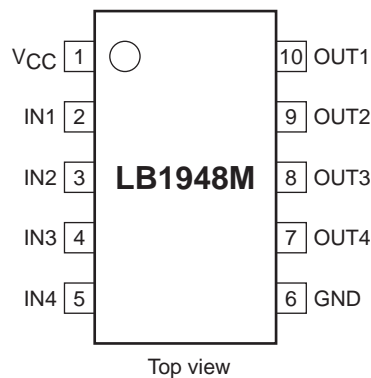
Package Dimensions

unit : mm (typ)

3086B



Pin Assignment

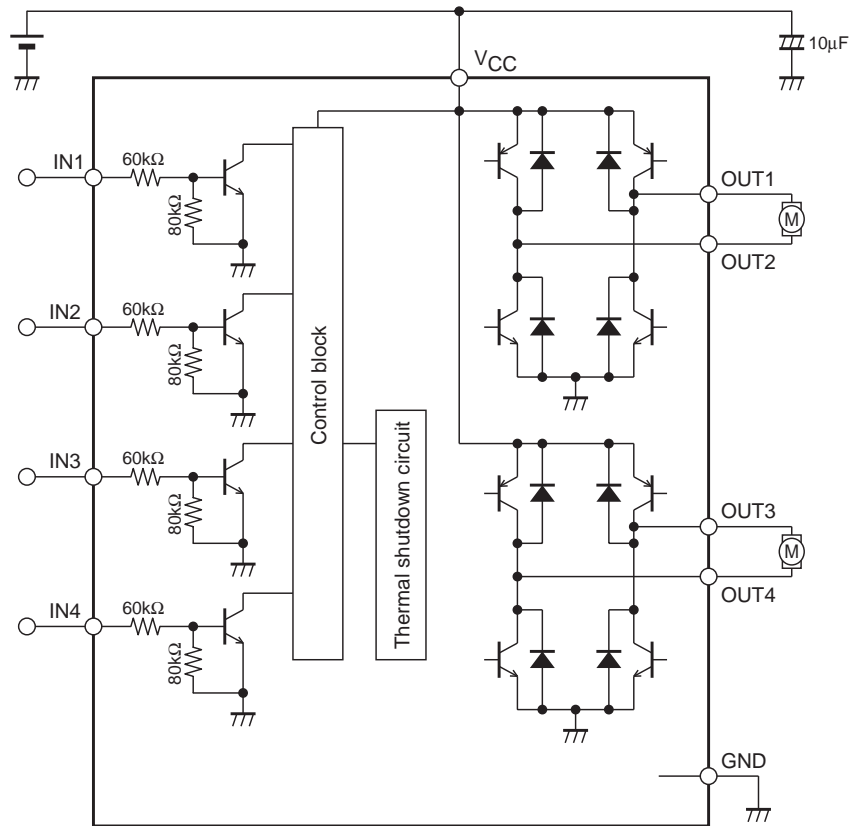


LB1948M

Truth Table

Input				Output				Notes	
IN1	IN2	IN3	IN4	OUT1	OUT2	OUT3	OUT4		
L	L	L	L	OFF	OFF	OFF	OFF	1CH	Standby mode
L	L			OFF	OFF				Standby mode
H	L			H	L				Forward
L	H			L	H				Reverse
H	H			L	L				Brake
		L	L			OFF	OFF	2CH	Standby mode
		H	L			H	L		Forward
		L	H			L	H		Reverse
		H	H			L	L		Brake

Block Diagram



LB1948M

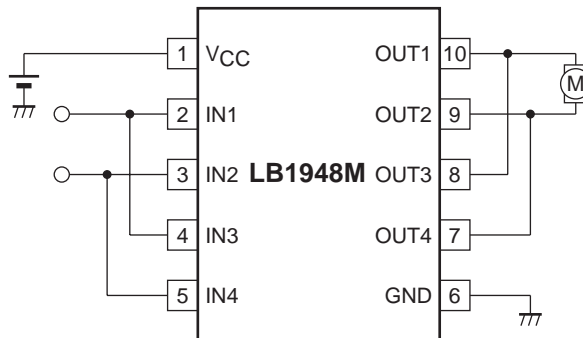
Design Documentation

(1) Voltage magnitude relationship

There are no restrictions on the magnitude relationships between the voltages applied to V_{CC} and IN1 to IN4.

(2) Parallel connection

The LB1948M can be used as a single-channel H-bridge power supply by connecting IN1 to IN3, IN2 to IN4, OUT1 to OUT3, and OUT2 to OUT4 as shown in the figure. ($I_{Omax} = 1.6A$, $V_O(sat) = 0.6V$ (typical) at $I_O = 800mA$)



(3) Observe the following points when designing the printed circuit board pattern layout.

- Make the V_{CC} and ground lines as wide and as short as possible to lower the wiring inductance.
- Insert bypass capacitors between V_{CC} and ground mounted as close as possible to the IC.
- Resistors of about $10K\Omega$ must be inserted between the CPU output ports and the IN1 to IN4 pins if the microcontroller and the LB1948M are mounted on different printed circuit boards and the ground potentials differ significantly.

Thermal Shutdown Temperature

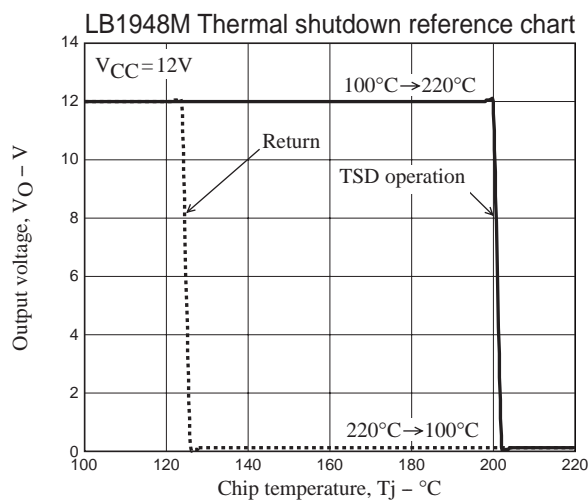
(1) Thermal shutdown temperature

The thermal shutdown temperature T_{sd} is $200 \pm 20^\circ C$ with fluctuations.

(2) Thermal shutdown operation

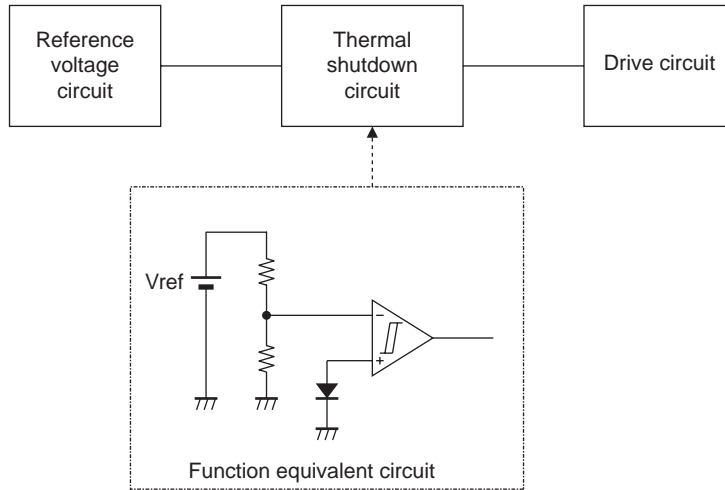
The operation of the thermal shutdown circuit is shown in the figure below.

When the chip temperature T_j is in the direction of increasing (solid line), the output turns off at approximately $200^\circ C$. When the chip temperature T_j is in the direction of decreasing (dotted line), the output turns on (returns) at approximately $125^\circ C$.



LB1948M

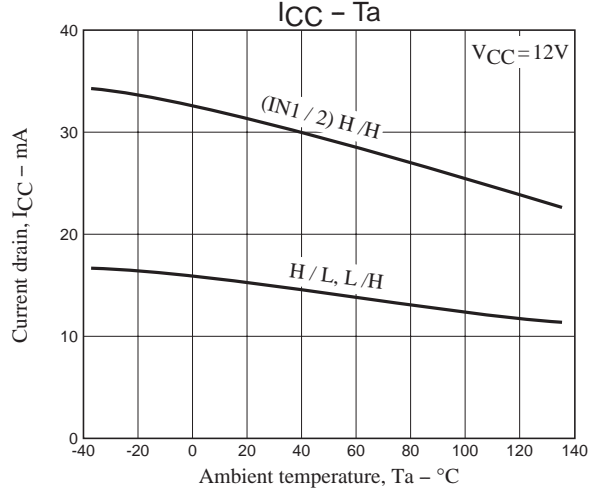
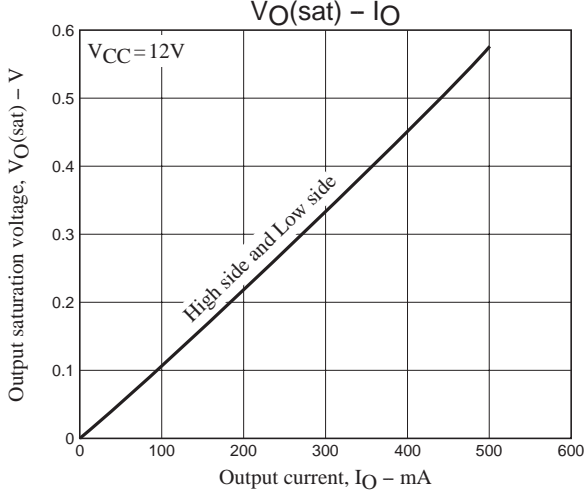
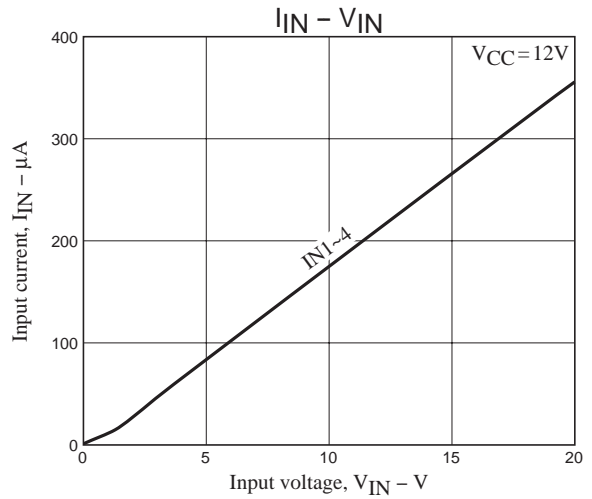
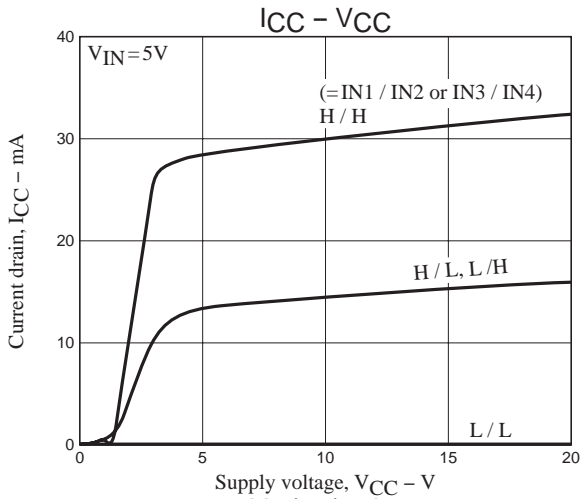
Thermal Shutdown Circuit Block Diagram

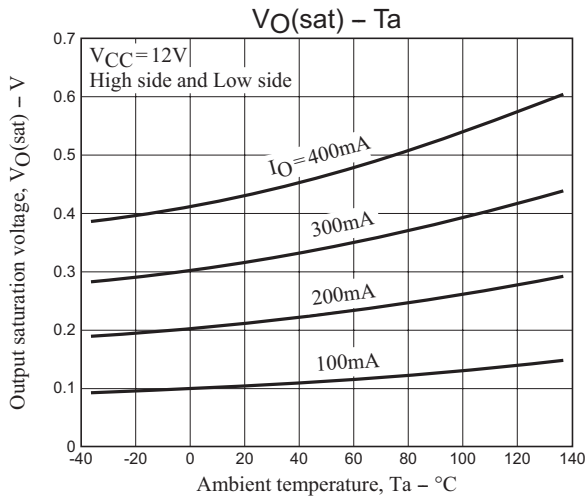


Note: The above is an example of thermal shutdown circuits although there are some differences from the actual internal circuit.

Thermal Shutdown Operation

The thermal shutdown circuit compares the voltage of the heat sensitive element (diode) with the reference voltage and shuts off the drive circuit at a certain temperature to protect the IC chip from overheating.





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